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### AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1-3. (Cancelled).

4. (Currently amended): A method of producing a group III-nitride semiconductor substrate, essentially consisting of:

a first step of forming a low-temperature buffer layer consisting of

$B_xAl_yGa_zIn_{1-x-y-z}N$  ( $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ,  $0 \leq 1-x-y-z \leq 1$ ), on a  $ZrB_2$  single crystal base having a defect density of  $10^7 \text{ cm}^{-2}$  or less, at a base temperature which does not give an energy greater than a surface potential of said  $ZrB_2$  single crystal base to a nitrogen atom arising from decomposition of buffer layer forming gas, allowing said low-temperature buffer layer to be grown or deposited on said  $ZrB_2$  single crystal base substantially without creation of any  $Zr-B-N$  amorphous nitrated layer as a result of diffusion and/or chemical bonding of the nitrogen atom, wherein said low-temperature buffer layer has a thickness in the range of 10 nm to  $1 \mu\text{m}$  capable of suppressing the nitriding of the surface of said  $ZrB_2$  single base, and said low-temperature buffer layer is formed as a single crystal at the time said first step is completed; and

a second step of successively to said first step, growing a single crystal film consisting of  $B_aAl_bGa_cIn_{1-a-b-c}N$  ( $0 \leq a \leq 1$ ,  $0 \leq b \leq 1$ ,  $0 \leq c \leq 1$ ,  $0 \leq 1-a-b-c \leq 1$ ), directly on said low-temperature buffer layer, to form a semiconductor layer consisting of